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PATENT & TRADEMARK OFFICE  
YAO-3950

PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yoshihisa Nagano et al. : Art Unit: 2815  
Serial No.: 09/103,873 : Examiner: J. Diaz  
Filed: June 24, 1998 :  
For: SEMICONDUCTOR DEVICE AND :  
METHOD FOR FABRICATING THE SAME

AMENDMENT AND REQUEST FOR EXTENSION OF TIME

Assistant Commissioner for Patents  
Washington, DC 20231

SIR:

Responsive to the Official Action dated January 30, 2001, please amend the above-identified application as follows:

CLAIMS:

Please replace claim 1 with the following amended claim:

1 A semiconductor device, comprising:  
2 a capacitor provided on a supporting substrate having an integrated  
3 circuit thereon and including a lower electrode, a dielectric film, and an upper  
4 electrode;  
5 a first interlayer insulating film provided so as to directly cover the  
6 capacitor;  
7 a first interconnect selectively provided on the first interlayer  
8 insulating film and electrically connected to the integrated circuit and the  
9 capacitor through a first contact hole formed in the first interlayer insulating  
10 film;  
11 a second interlayer insulating film having a tensile stress provided  
12 so as to directly cover the first interconnect and the first interlayer insulating  
13 film;